

IN THE CLAIMS:

Please amend claims 2, 5-7, and 9-12 as follows:

1. (Withdrawn): A method of forming a thin film transistor, comprising:

forming a buffer layer on a transparent substrate;

forming an amorphous silicon layer on the buffer layer;

crystallizing the amorphous silicon layer into a polysilicon layer using a sequential lateral solidification (SLS) method;

patterning the polysilicon layer to form a polysilicon active layer;

performing a rapid thermal annealing (RTA) process to the polysilicon active layer under a H₂ atmosphere;

performing a rapid thermal oxidation (RTO) process to form a silicon-oxidized layer on the polysilicon active layer after the RTA process; and

forming a metal layer over the transparent substrate to cover the silicon-oxidized layer.

2. (Currently Amended): A [[The]] method of forming a thin film transistor, according to claim 1, further comprising:

forming a buffer layer on a transparent substrate;

forming an amorphous silicon layer on the buffer layer;

crystallizing the amorphous silicon layer into a polysilicon layer using a sequential lateral solidification (SLS) method;

patterning the polysilicon layer to form a polysilicon active layer;

performing a rapid thermal annealing (RTA) process to the polysilicon active layer under a H₂ atmosphere;

performing a rapid thermal oxidation (RTO) process to form a silicon-oxidized layer on the polysilicon active layer after the RTA process;

forming a metal layer over the transparent substrate to cover the silicon-oxidized layer;

patterning the metal layer to form a gate electrode over the polysilicon active layer;

doping n-type ions to form lightly doped drain (LDD) regions in the polysilicon active layer on both sides of the gate electrode, and doping p-type ions to ohmic contact regions outside the LDD regions doping the polysilicon active layer with impurities using the gate electrode as a doping mask to form ohmic contact regions;

forming an interlayer insulator over the transparent substrate to cover the gate electrode;

patterning the interlayer insulator to form first and second contact holes exposing the ohmic contact regions;

forming source and drain electrodes on the interlayer insulator, the source and drain electrodes contacting the ohmic contact regions, respectively, through the first and second contact holes;

forming a passivation layer on the interlayer insulation to cover the source and drain electrodes, wherein the passivation layer has a drain contact hole that exposes a portion of the drain electrode; and

forming a pixel electrode on the passivation layer, the pixel electrode contacting the drain electrode through the drain contact hole.

3. (Original): The method according to claim 2 , wherein the patterning the metal layer includes patterning the silicon-oxidized layer into the same shape as the gate electrode.

4. (Original): The method according to claim 2, wherein the interlayer insulator is formed of one of silicon oxide and silicon nitride.

5. (Currently Amended): The method according to claim ~~[[1]]~~ 2, wherein the RTA and RTO processes are conducted at a temperature in the range of about 500 to 1000 degrees Celsius (°C).

6. (Currently Amended): The method according to claim [[1]]2, wherein the RTA and RTO processes are conducted for less than 60 minutes.

7. (Currently Amended): The method according to claim [[1]]2, wherein the RTO process is conducted under an oxygen-based atmosphere.

8. (Original): The method according to claim 7, wherein the oxygen-based atmosphere includes at least one of O₂, N₂O, and NO.

9. (Currently Amended): The method according to claim [[1]]2, further comprising dehydrogenating the amorphous silicon layer before crystallizing the amorphous silicon layer.

10. (Currently Amended): The method according to claim [[1]]2, wherein the metal layer is selected from the group consisting of aluminum (Al), aluminum alloy (Al-alloy), and molybdenum (Mo).

11. (Currently Amended): The method according to claim [[1]]2, wherein the crystallizing the amorphous silicon layer generates a plurality of protuberances of the polysilicon layer.

12. (Currently Amended): The method according to claim [[1]]2, wherein the RTA process blunts and flattens the protuberances of the polysilicon layer.